EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	etch$4 near9 ("ILD" or "interlevel dielectric") near9 (cap or metal) and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and (partial$4 near9 (cap or metal)) and (substrate or semiconductor or wafer) and gas and (438/622.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 12:48
S1	54	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:12
S2	0	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and "metal layer" and ("tantalum nitride" or "TaN") and depositon and argon and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S3	0	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and ("tantalum nitride" or "TaN") and depositon and argon and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S4	35	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S5	15	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55

EAST Search History

S6	4	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S7	2	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and (argon near4 nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:56
S8	2	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and (argon near4 nitrogen) and deposit$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:41
S9	0	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and degass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42
S10	0	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and degass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42
S11	4	("ILD" or "interlevel dielectric") and etch$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and degas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42
S12	531	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:14

EAST Search History

S13	462	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:14
S14	63	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:14
S15	0	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and degas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:14
S16	27	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:18
S17	0	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct$4) and degas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:19
S18	27	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct$4) and remov$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:19
S19	6	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct$4) and (remov$4 near8 gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:22

EAST Search History

S20	20	"ILD" and etch and ("SiC" or "silicon carbide" or "SiN" or "silicon nitride") and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct$4) and (remov$4 near8 gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 10:34
S21	18	(("ILD" or "interlevel dielectric") near4 etch$4) and (partial$2 near8 cap) and gas and (liner or barrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 12:47
S22	11	(("ILD" or "interlevel dielectric") near4 etch$4) and (partial$2 near8 cap) and gas and ("SiC" or "silicon carbide" or "SiN" or "silicon nitride") and liner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 12:53
S23	0	(("ILD" or "interlevel dielectric") near4 etch$4) and (partial$2 near8 cap) and gas and ("SiC" or "silicon carbide" or "SiN" or "silicon nitride") and liner and (438/622.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 12:53
S24	241	(partial$4 near4 etch) near8 (metal or cap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 10:37
S25	34	(partial$4 near4 etch) near8 (metal or cap) and ("ILD" or "interlevel dielectric")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/25 10:37
S26	3771	etch$4 near9 ("ILD" or "interlevel dielectric")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:04

S27	922239	etch$4 near9 ("ILD" or "interlevel dielectric") near "9" cap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:04
S28	91	etch$4 near9 ("ILD" or "interlevel dielectric") near9 cap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:05
S29	66	etch$4 near9 ("ILD" or "interlevel dielectric") near9 cap and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:06
S30	24	etch$4 near9 ("ILD" or "interlevel dielectric") near9 cap and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and (liner near9 ("ILD" or "interlevel dielectric"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:07
S31	2	etch$4 near9 ("ILD" or "interlevel dielectric") near9 cap and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and (liner near9 ("ILD" or "interlevel dielectric")) and ((semiconductor or substrate or wafer) near9 (inert near gas))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:08
S32	7	etch$4 near9 ("ILD" or "interlevel dielectric") near9 cap and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and (liner near9 ("ILD" or "interlevel dielectric")) and ((semiconductor or substrate or wafer) near9 gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:27

S33	8	etch$4 near9 ("ILD" or "interlevel dielectric") near9 (cap or metal) and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and (liner near9 ("ILD" or "interlevel dielectric")) and ((semiconductor or substrate or wafer) near9 gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:33
S34	570	etch$4 near9 ("ILD" or "interlevel dielectric") near9 (cap or metal) and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:34
S35	52	etch$4 near9 ("ILD" or "interlevel dielectric") near9 (cap or metal) and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and ((substrate or wafer or semniconductor) near9 gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 08:34
S36	14	etch$4 near9 ("ILD" or "interlevel dielectric") near9 (cap or metal) and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and ((substrate or wafer or semniconductor) near9 gas) and liner	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:02
S37	570	etch$4 near9 ("ILD" or "interlevel dielectric") near9 (cap or metal) and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:05
S38	82	etch$4 near9 ("ILD" or "interlevel dielectric") near9 (cap or metal) and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and (partial$4 near9 (cap or metal))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 10:06
S39	49	etch$4 near9 ("ILD" or "interlevel dielectric") near9 (cap or metal) and (open$3 or via or hole or trench) near9 ("ILD" or "interlevel dielectric") and (partial$4 near9 (cap or metal)) and (substrate or semiconductor or wafer) and gas	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 12:47